Joint International Conference on
The 8th ICMAP & The 9th ISFM

January 17-20, 2021 l Online Conference

[TC4] Plasma Deposition and Etching - II (GWP, Thermal, ALE, MTJ, DFT)	
Date / Time	January 19 (Tue.), 2021 / 16:30-18:50
Place	Channel C
Session Chair(s)	Se Hun Kwon (Pusan Nat'l Univ., Korea)

[TC4-1] **16:30-16:50**

Etch Characteristics of SiO_2 Using Lower Global Warming C_xF_8 (x=5,7) Inductively Coupled Plasmas

Da In Sung, Geun Young Yeom, Dong Woo Kim, and Hyun Woo Tak
Sungkyunkwan Univ., Korea

[TC4-2] **16:50-17:10**

Influence of Carbon Source Gas Flow Rate on High-rate Deposition of Polycrystalline Diamond Film Using Time-Series Exposure of Modulated/Non-Modulated Induction Thermal Plasmas

Kazufumi Hata, Naoki Kano, Yusuke Nakano, Yasunori Tanaka, and Tatsuo Ishijima
Kanazawa Univ., Japan

[TC4-3] **17:10-17:30**

Atomic Layer Etching of SiO_2 and Si_3N_4 with Fluoroether and Fluoroalcohol Compounds

Yongjae Kim, Yebin Lee, Seonghyeon Lee, and Heeyeop Chae
Sungkyunkwan Univ., Korea

[TC4-4] **17:30-17:50**

Study on Etch Characteristics of Magnetic Tunnel Junction (MTJ) Materials Using Hydrogen Based Reactive Ion Beam

Yun Jong Jang, Doo San Kim, Ju Eun Kim, Ye Eun Kim, You Jung Gill, and Geun Young Yeom
Sungkyunkwan Univ., Korea

[TC4-5] **17:50-18:10**

Density Functional Theory Study on the Gas-phase Cleaning of SiO_2 Using HF and NH4F

Romel Hidayat[1], Tanzia Chowdhury[1], Hye-Lee Kim[1], Tirta Rona Mayangsari[2], Seongjae Cho[3], Sangjoon Park[4], Jongwan Jung[1], and Won-Jun Lee[1]
[1]Sejong Univ., Korea, [2]Pertamina Univ., Indonesia, [3]Gachon Univ., Korea, [4]Wonik IPS, Korea

[TC4-6] Keynote **18:10-18:50**

Needs of New Plasma Etching Technologies for the Next 10 Years' Chip Fabrication

Jong Chul Park
Samsung Electronics Co., Ltd., Korea